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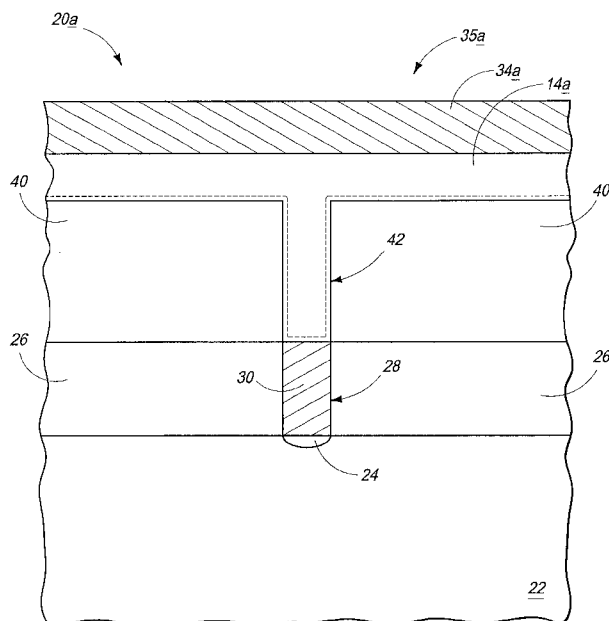
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(54) Title: METHODS OF FORMING PHASE CHANGE MATERIALS AND METHODS OF FORMING PHASE CHANGE MEMORY CIRCUITRY



(57) Abstract: A method of forming a phase change material which having germanium and tellurium therein includes depositing a germanium-containing material over a substrate. Such material includes elemental-form germanium. A gaseous tellurium-comprising precursor is flowed to the germanium-comprising material and tellurium is removed from the gaseous precursor to react with the elemental-form germanium in the germanium-comprising material to form a germanium and tellurium-comprising compound of a phase change material over the substrate. Other implementations are disclosed.

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